Arts, Commerce and Science College, Bodwad.

Question Bank

S.Y. B.Sc. Sem-III

Subject: - PHY 302 (A): Electronics -I

Multiple Choice Questions

Unit 1

Semiconductor diodes

Multiple Choice Questions for one mark

1. The arrow direction in the diode symbol indicates.....

a) Direction of electron flow.

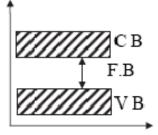
b) Direction of hole flow (Direction of conventional current)

- c) Opposite to the direction of hole flow
- d) None of the above
- 2. The knee voltage (cut in voltage) of Si diode is.....
 - a) 0.2 V b) 0.7 V c) 0.8 V d) 1.0 V
- 3. When the diode is forward biased, it is equivalent to.....
- a) An off-switch b) An On-switch c) A high resistance d) None of the above
- 4. Under normal reverse bias voltage applied to diode, the reverse current in Si diode......
- a) 100 mAb) order of μAc) 1000 μAd) None of these5. Avalanche breakdown in a diode occurs when.....
 - a) Potential barrier is reduced to zero. b) Forward current exceeds certain value.

c) Reverse bias exceeds a certain value. d) None of these

- 6. Reverse saturation current in a Silicon PN junction diode nearly doubles for very.....
 - a. 20 rise in temp. b. 50 rise in temp. c. 60 rise in temp. d. 100 rise in temp.
- 7. A forward potential of 10V is applied to a Si diode. A resistance of 1 K Ω is also in series with the diode. The current is.....
 - a. 10 mA **b. 9.3 mA** c. 0.7 mA d. 0 mA
- 8. Barrier potential at the room temperature (250 C) is 0.7V, its value at 1250 C is.....
 - **a. 0.5 V** b. 0.3 V c. 0.9 V d. 0.7 V

9. When a reverse bias is applied to a diode, it will..... a. Raise the potential barrier b. Lower the potential barrier c. Increases the majority-carrier a current greatly d. None of these 10. The best description of zener diode is that a. it operates in reverse region b. it is a constant voltage device c. it is a constant current device d. none of the above 11. The LED is usually made of..... a. GeSi b. C and Si c. GaAs d. none of the above 12. The P-N junction photodiode operates a. first forward biasing the junction and then illuminating it. b. first reverse biasing the junction and then illuminating it. c. first illuminating the junction and then reverse biasing it. d. first illuminating the junction and then forward biasing it. 13. Testing a good diode with an ohmmeter should indicate a. high resistance when forward or reverse biased b. low resistance when forward or reverse biased c. high resistance when reverse biased and low resistance when forward biased d. high resistance when forward biased and low resistance when reverse biased 14. A P-N junction allows current flow when..... a. both the n-type and p-type materials have the same potential b. the n-type material is more positive than the p-type material c. the p-type material is more positive than the n-type material d. there is no potential on the n-type or p-type materials 15. The diode used in seven segment display is..... b. Photo diode a. zener diode c. LED d. LASER diode 16. The diagram shown below corresponds to,



(a)	the	single	energy	level	of	an	electron.
$\langle \cdot \cdot \rangle$					<u> </u>		••••••

- (b) the discrete energy level of an electron.
- (c) the energy transfer diagram.

(d) the energy band diagram.

17. The space between the outermost filled energy band and the next empty band is called

(a) valence band (b) conduction band (c) forbidden zone (d) none of these

18. The forward biased resistance of the diode isthan its reverse biased resistance. (c) smaller (a) larger (b) double (d) none of these 19. A zener diode is operated in (a) breakdown region (b) forward characteristics region (d) none of these (c) zero biasing 20. If the p-n junction diode is heavily doped then breakdown voltage will (a) increases (b) decreases (c) remains same (d) none of these 21. Solar cell works on the principle of..... (a) photo thermal conversion (b) Photovoltaic conversion (c) electron pumping (d) none of these 22. For artificial satellite the source of energy is..... (a) fuel cell (b) Edison cell (c) solar cell (d) biological cell 23. The electrical behavior of a solid material is determined by..... (a) the energy band gap (b) the energy levels of inner shell electrons (d) none of these (c) zero biasing 24. The barrier potential for an unbiased silicon junction diode at room temperature is..... b. 0.7 V a. 0.2 V c. 0.8 V d. 1.0 V 25. A zener diode is used as a..... (b) half wave rectifier (a) half wave regulator (c) voltage regulator (d) amplifier 26. In operation, a photo diode is (a) unbaised (b) always forward biased (c) always reverse biased (d) either forward or reverse biased

27. A photo diode is used in					
(a) a break indicator	(b) an optocoupler				
(c) a regulated power supply	(d) a logic gate				
28. The acronym LED stands for					
(a) light energized diode	(b) light emitting diode				
(c) low energy device	(d) low energy dynamo				
29. The arrow direction in the diode symbol	indicates				
a. Direction of electron flow.	b. Direction of hole flow (Direction of conventional current)				
c. Opposite to the direction of hole fl	low d. None of the above				
30. When the diode is forward biased, it is equivalent to					
a. An off-switch b. An On-swi	tch c. A high resistance d. None of the above				
31. By addingimpurity in intrinsic se	miconductor P type semiconductor is made.				
a. trivalent b. pentavalent	c. quadra valant d. divalent				
32. The charge on P-type semiconductor is					
a. positive b. neutral c. nega	tive d. either positive or negative				
33. From the following semiconductor diodes, onlyoperates in forward bias only.					
a. LED b. zener	c. photdiode d. None of the above				

Unit 2

Rectifiers and power supplies

Multiple Choice Questions	for ONE (01) marks					
1.In a half rectification diod	e conducts during					
a. both half cycles	b. positive half	c. negative half	d. one half input			
2.A full-wave rectifier is	efficient than a	half wave rectifier.				
a. more	b. less	c. equal	d. none of the above			
3.In full-wave rectification,	if i/p frequency is 50 H	Iz then output frequen	cy is			
a. 50 Hz	b.100 Hz	c. 200 Hz	d. 400 Hz			
4.Ripple factor of a full way	e rectifier is					
a.0.58	b. 0.48	c. 0.28	d. 0.38			
5.The maximum efficiency	of a full-wave rectifier	is				
a. 41.2 %	b. 31.2 %	c. 91.2 %	d. 81.2 %			
6.In half-wave rectification if i/p frequency is 50 Hz, then o/p frequency is						
a. 50 Hz	b.100 Hz	c. 250Hz	d. 25 Hz			
7.In a half wave rectifier, the load current flows for						
a. the complete cycle of the input signal.						
b. only for the positive half-cycle of the input signal.						
c. less than half cycle of the i/p signal.						
d. more than half cycle but less than the complete cycle of the input signal.						
8. The RMS value of a half wave rectifier current is 10 A. Its value for full wave rectification						
current would be						
a. 10 A	b .14.14 A	c. (20/π) A	d. 20 A.			
9. The ripple factor of a full-wave rectifier circuit compared to that of a half wave rectifier circuit						
without filter is						

a) half of that for a half 'wave rectifier b) less than half that for a half-wave rectifier circuit c) equal to that of a half wave rectifier d) none of the above. 10. Filter circuits after rectifiers..... a. smoothens pulsation b. hardens pulsation d. doubles the pulsations c. keeps the pulsation as it is 11. is not an essential element of d. c. power supply. a) Rectifier b) Filter c) Voltage Regulator d) Voltage Amplifier 12. A voltage regulator is a circuit which..... a. Converts the d. c. voltage into a. c. voltage. b. Smoothens the ac variations in d. c. output voltage. c. Maintains a constant dc output voltage in spite of the fluctuations in a. c. input voltage or load current. d. None of the above. 13. The % load regulation of a power supply providing 100V unloaded and 95V at full load is..... a) 5.26 % b) 5.0% c) 0.526% d) None of the above 14. The main function of a voltage regulator is to provide a nearly...... output voltage. a) Sinusoidal b) constant c) smooth d) fluctuating

Unit 3

Bipolar Junction Transistors

Multiple Choice Questions for ONE (01) mark

1) A transistor hasPN junctions.							
a. one	b. two)	c. three	d. four			
2) The emitter is	doped.						
a. heavily	b. ligh	tly	c. moderately	d. not			
3) The base is	doped.						
a. heavily	b. ligh	ntly	c. moderately	d. not			
4) The collector is .	doped.						
a. heavily	b. ligl	ntly	c. moderately	d. not			
5) The value of α is	š						
a. less than 1 b. greater than1c. less than 0d. equal to 0							
6) The main function of a transistor is to do							
a. rectification b. amplification c. light emission d. heat emission							
7) Transistors would be classified as electronic devices.							
a. active b. passive c. both active and passive d. neither active nor passive							
8) The emitter- base junction of a bipolar transistor is							
a. always reverse biased b. forward biased or reverse biased							
c. always forward biased d. neither forward or reverse biased							
9) From working of transistor operation one can write							
a. IB =IC+I	E b. IC	=IB+IE	c.IE =IC-IB	d. IE =IC+IB			
10) For CE transistor configuration o/p characteristics is graph of							
a. IB verses VBE b. IB verses VCE c.IE verses VCE d. IC verses VCE							
11) For proper working of transistor							

a) EB junction should be forward biased and CB junction should be reverse biased

- b) EB junction should be reverse biased and CB junction should be forward biased
- c) EB junction and CB junction should be reverse biased
- d) EB junction and CB junction should be forward biased

Unit 4

Digital electronics

Multiple Choice Questions for ONE (01) mark

	1.	А	logic	circuit	is	an	electro	onic	circuit	which
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- (a) makes logic decision
- (b) allows electron flow only in one direction
- (c) works on binary algebra
- (d) Alternates between 0 and 1 values.
- 2. An Ex-OR gate produces an output only when its two inputs are

(a) high	(b) low	(c) different	(d) same
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3. An AND gate

(a) implements logic addition

- (b) is equivalent to a series switching circuit
- (c) is an any-or-all gate
- (d) is equivalent to a parallel switching circuit
- 4. When an input electrical signal A = 10100 is applied to a NOT gate, its output signal is

(a) 01011 (b) 10101 (c) 10100	(d) 00101
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- 5. The only function of a NOT gate is to
 - (a) stop a signal (b) recomplement a signal
 - (c) invert an input signal (d) acts as a universal gate.
- 6. A NOR gate is ON only when all its inputs are
 - (a) ON (b) positive (c) high (d) OFF
- 7. The output of two input OR gate is high
 - (a) Only if both inputs are high
 - (b) Only if both inputs are low

(c) Only if one input is high and other is low

(d) If at least one of the input is high

8. The output of two input AND gate is high

(a) Only if both inputs are high

- (b) Only if both inputs are low
- (c) Only if one input is high and other is low
- (d) If at least one of the input is low
- 9. The output of two input NOR gate is high
 - (a) Only if both inputs are high

(b) Only if both inputs are low

- (c) Only if one input is high and other is low
- (d) If at least one of the input is high
- 10. The output of two input NAND gate is high
 - (a) Only if both inputs are high
 - (b) Only if both inputs are low

(c) Only if one input is high and other is low

- (d) If at least one of the input is low
- 11. A digital word has even parity
 - (a) If it has even number of 1's
 - (b) If it has even number of 0's
 - (c) If the decimal value of digital word is even
 - (d) None of these
- 12. An Ex-OR gate gives a high output

(a) If there are odd number of 1's in the input

- (b) If there are even number of 1's in the input
- (c) If there are odd number of 0's in the input
- (d) If there are even number of 0's in the input
- 13. The gate ideally suited for bit comparison is
 - (a) Two input Ex-OR gate
 - (b) Two input Ex-NOR gate
 - (c) Two input NOR gate

(d) Two input NAND gate							
14. The total number of input states for 4-input OR gate is							
(a) 20	(b) 16	(c) 12	(d) 8				
15. In a 4-input AND	15. In a 4-input AND gate, the total number of High outputs for 16 input sates are						
(a) 16	(b) 8	(c)4	(d)1				
16. In a 4-input OR g	ate, the total number of	f High outputs for 16 in	put sates are				
(a) 16	(b) 15	(c)8	(d) 1				
17. Which of these ar	e universal gates						
(a) only NOR		(b) only					
(c) Both NOF	and NAND	(d) both OR an	nd AND				
18. Two voltages are	-5 V and -10 V. In pos	sitive logic					
(a) -5 V is 1 a	nd -10 V is 0						
(b) -10 V is 1 and -5 V is 0							
(c) -5 V is 1 in some circuits and 0 in others							
(d) -10 V is 1 in some circuits and 0 in others							
19. On a K-map, grouping of 0s produces,							
a) POS expressions							
b) a SOP expressions							
c) a "don't care condition"							
d) AND-OR logic.							
20 is the base of	binary number system	n.					
a) 2	d)16						
21. The decimal number system consist of digit.							
a) 2 b) 4 c) 16 d)							
22. The method used for decimal to binary conversion is called as							
a) double dat			b) decimal dabble method				
c) binary dabble method d) stream line method							
-	R gate is high when						
a) all its input	-	_	b) all its inputs are low				
c) any one of i	its input is high	c) any one of it	c) any one of its input is low				

24. If input of EX-OR gate $A = 1$ and $B = X$ then Y is						
a) 0	b) X	c) X	d) XX			
25. The output of NAND gate is zero when						
a) all its inpu	its inputs are one					
c) any one of its input is zero			one of its input is one			

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